

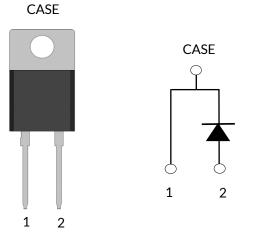


# 10A -1200V SiC Schottky Diode

Rev. C, February 2020

# DATASHEET

# UJ3D1210TS



Part Number	Package	Marking
UJ3D1210TS	TO-220-2L	UJ3D1210TS



#### Description

UnitedSiC offers the 3<sup>rd</sup> generation of high performance SiC Merged-PiN-Schottky (MPS) diodes. With zero reverse recovery charge and 175°C maximum junction temperature, these diodes are ideally suited for high frequency and high efficiency power systems with minimum cooling requirements.

#### Features

- Maximum operating temperature of 175°C
- Easy paralleling
- Extremely fast switching not dependent on temperature
- No reverse or forward recovery
- Enhanced surge current capability, MPS structure
- Excellent thermal performance, Ag sintered
- 100% UIS tested
- AEC-Q101 qualified

## **Typical applications**

- Power converters
- Industrial motor drives
- Switch mode power supplies
- Power factor correction modules





# Maximum Ratings

Parameter	Symbol	<b>Test Conditions</b>	Value	Units		
DC blocking voltage	V <sub>R</sub>		1200	V		
Repetitive peak reverse voltage, T <sub>J</sub> =25°C	V <sub>RRM</sub>		1200	V		
Surge peak reverse voltage	V <sub>RSM</sub>		1200	V		
Maximum DC forward current	I <sub>F</sub>	T <sub>C</sub> = 157°C	10	А		
Non-repetitive forward surge current	1	T <sub>C</sub> = 25°C, t <sub>p</sub> = 10ms	120	^		
sine halfwave	I <sub>FSM</sub>	T <sub>C</sub> = 110°C, t <sub>p</sub> = 10ms	110	A		
Repetitive forward surge current		T <sub>C</sub> = 25°C, t <sub>p</sub> = 10ms	54.2	А		
sine halfwave, D=0.1	I <sub>FRM</sub>	T <sub>C</sub> = 110°C, t <sub>p</sub> = 10ms	32.3			
Non-repetitive peak forward current	I <sub>F,max</sub>	T <sub>C</sub> = 25°C, t <sub>p</sub> = 10μs	720	А		
		$T_{\rm C}$ = 110°C, $t_{\rm p}$ = 10µs	720			
-2 .	∫i <sup>2</sup> dt —	T <sub>C</sub> = 25°C, t <sub>p</sub> = 10ms	72	A <sup>2</sup> s		
i <sup>2</sup> t value		$T_{\rm C} = 110^{\circ}{\rm C}, t_{\rm p} = 10{\rm ms}$	60			
Power dissipation	P <sub>tot</sub> —	T <sub>C</sub> = 25°C	220.6	W		
		T <sub>C</sub> = 157°C	26.5			
Maximum junction temperature	T <sub>J,max</sub>		175	°C		
Operating and storage temperature	T <sub>J</sub> , T <sub>STG</sub>		-55 to 175	°C		
Soldering temperatures, wavesoldering only allowed at leads	T <sub>sold</sub>	1.6mm from case for 10s	260	°C		

# **Thermal Characteristics**

Parameter	Symbol	Test Conditions	Value			Units
			Min	Тур	Max	Units
Thermal resistance, junction-to-case	$R_{ ext{ hetaJC}}$			0.52	0.68	°C/W



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### Electrical Characteristics (T<sub>J</sub> = +25°C unless otherwise specified)

Parameter	Symbol	Test Conditions	Value			Linite
			Min	Тур	Max	- Units
Forward voltage	V <sub>F</sub>	I <sub>F</sub> = 10A, T <sub>J</sub> =25°C	-	1.4	1.6	V
		I <sub>F</sub> = 10A, T <sub>J</sub> =150°C	-	1.85	2.3	
		I <sub>F</sub> = 10A, T <sub>J</sub> =175°C	-	2	2.6	
Devices a summer t	I <sub>R</sub>	V <sub>R</sub> =1200V, T <sub>J</sub> =25°C	-	10	110	μΑ
Reverse current		V <sub>R</sub> =1200V, T <sub>J</sub> =175°C	-	450		
Total capacitive charge <sup>(1)</sup>	Q <sub>c</sub>	V <sub>R</sub> =800V		51		nC
Total capacitance	С	$V_R$ =1V, f = 1MHz		510		pF
		V <sub>R</sub> =400V, f = 1MHz		48		
		V <sub>R</sub> =800V, f = 1MHz		41		
Capacitance stored energy	E <sub>C</sub>	V <sub>R</sub> =800V		15		μJ

(1)  $Q_c$  is independent on  $T_J$ ,  $di_F/dt$ , and  $I_F$  as shown in the application note USCi\_AN0011.

#### **Typical Performance Diagrams**

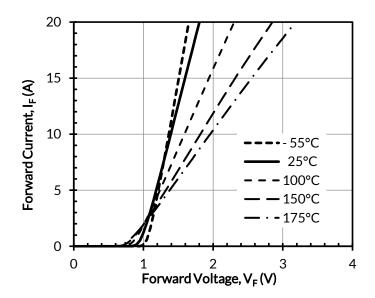


Figure 1. Typical forward characteristics

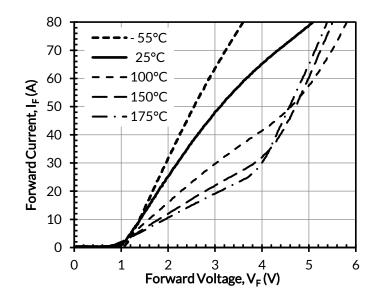
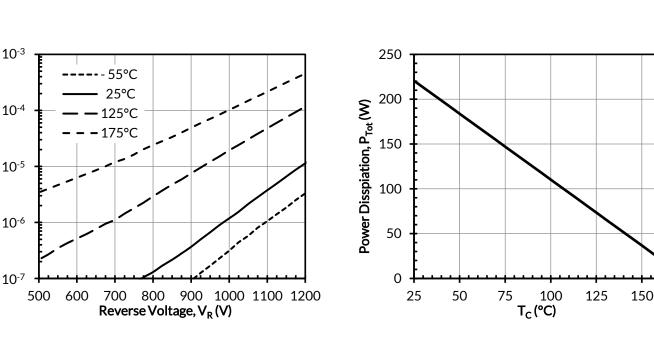


Figure 2. Typical forward characteristics in surge current



Reverse Current, I<sub>R</sub> (A)



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Figure 3. Typical reverse characteristics

Figure 4. Power dissipation

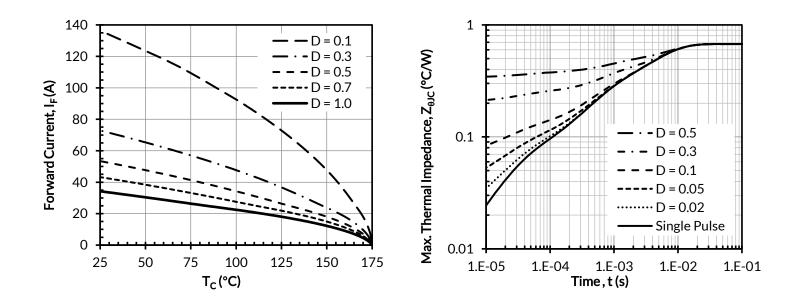


Figure 5. Diode forward current

Figure 6. Maximum transient thermal impedance





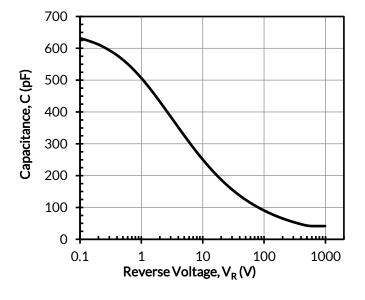


Figure 7. Capacitance vs. reverse voltage at 1MHz

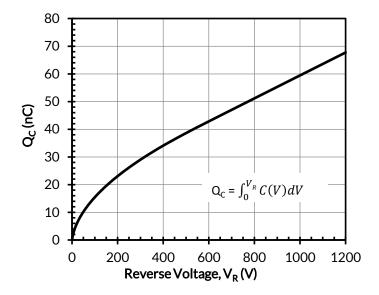


Figure 8. Typical capacitive charge vs. reverse voltage

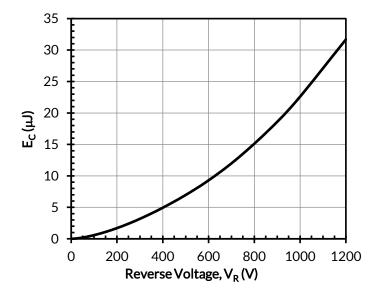


Figure 9. Typical capacitance stored energy vs. reverse voltage









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